

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application:

#### **Listing of Claims:**

Claims 1-26 (Canceled)

Claim 27 (Currently Amended): A method for fabricating a semiconductor apparatus comprising:

forming a semiconductor integrated circuit on a first surface of a semiconductor substrate;

forming a base member of insulating material on the first surface of the semiconductor substrate;

forming a conductive layer directly on the first surface of the semiconductor substrate, the conductive layer being connected to the semiconductor integrated circuit and having an extended portion that extends onto a top surface of the base member;

placing the first surface of the semiconductor substrate having the semiconductor integrated circuit, the base member and the conductive layer thereon as facing a connection substrate;

connecting the extended portion of the conductive layer to the connection substrate; and

supplying a sealing member in a space between the two semiconductor substrate and the connection substrate, after said connecting,  
the base member and the sealing member having a same thermal expansion coefficient.

Claim 28 (Currently Amended): A method according to claim 27, wherein the base member and the sealing member are a ~~same material~~ polyimide resin.

Claims 29-30 (Canceled)

Claim 31 (New): A method according to claim 27, wherein the conductive layer is formed so that the extended portion extends onto an entirety of the top surface of the base member.